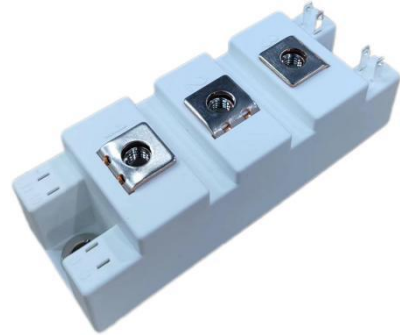


## 1200V 150A CoolFAST™ IGBT7 Power Module

**Electrical Features:**

- 1200V 150A,  $V_{CE(sat)} = 1.7V@25^{\circ}C$
- High RBSOA Capability
- Trench/FS Technology
- Low Reverse-recovery Losses
- High SC Capability

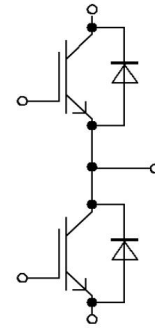


**Applications:**

- Motor Drives
- Solar Applications
- UPS Systems
- Commercial Electric Vehicles
- Wind Turbines

**Mechanical Features:**

- High Power and Thermal Cycling Capability
- Maximum Junction Temperature 175°C
- High Power Density
- PressFIT Contact Technology
- Isolated Base Plate



**Equivalent circuit**

**Maximum Ratings and Characteristics**

**Absolute Maximum Ratings at Tc= 25°C (unless otherwise specified)**

Items	Symbols	Values	Units	Remarks
Collector-Emitter voltage	$V_{CES}$	1200	V	
Gate-Emitter voltage	$V_{GES}$	±30	V	
DC Collector Current	$I_C$	150	A	$T_c = 100^{\circ}C$
Pulsed Collector Current	$I_{CP}$	300	A	Note *1
Diode Forward Current	$I_F$	150	A	
Repetitive Peak Forward Current	$I_{FRM}$	300	A	
Operating Junction Temperature	$T_{vj}$	-40 ~ +150	°C	
Storage Temperature	$T_{stg}$	-40 ~ +125	°C	

Note \*1 : Pulse width limited by  $T_{vjmax}$ .

**Electrical characteristics (unless otherwise specified)**
**IGBT, Inverter**

Description	Symbols	Conditions	Values			Unit	
			Min	Typ	Max		
Zero Gate Voltage Collector Current	$I_{CES}$	$V_{CE}= 1200V, V_{GE}= 0V$ $T_{vj}= 25^{\circ}C$			200	$\mu A$	
Gate-Emitter Leakage Current	$I_{GES}$	$V_{CE}= 0V, V= 20V, T_{vj}= 25^{\circ}C$			$\pm 300$	nA	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}= V_{GE}, I_C= 150mA$	6.2	6.7	7.2	V	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}= 15V$ $I_C= 150A$	$T_{vj}= 25^{\circ}C$		1.7	2.2	V
			$T_{vj}= 125^{\circ}C$		2.1		
			$T_{vj}= 150^{\circ}C$		2.2		
Input Capacitance	$C_{ies}$	$V_{CE}= 25V, V_{GE}= 0V$		40		nF	
Reverse Transfer Capacitance	$C_{res}$	$f= 1MHz$		0.19		nF	
Gate Charge	$Q_G$	$V_{CC}= 600V, V_{GE}= 15V$		1450		nC	
Internal Gate Resistor	$R_{Gint}$	$T_{vj}= 25^{\circ}C$		2.8		$\Omega$	
Turn-On Delay Time, Inductive load	$t_{d(on)}$		$T_{vj}= 25^{\circ}C$		0.36	$\mu s$	
			$T_{vj}= 125^{\circ}C$		0.39		
			$T_{vj}= 150^{\circ}C$		0.40		
Rise Time, Inductive load	$t_r$		$T_{vj}= 25^{\circ}C$		0.13	$\mu s$	
			$T_{vj}= 125^{\circ}C$		0.15		
			$T_{vj}= 150^{\circ}C$		0.16		
Turn-Off Delay Time, Inductive load	$t_{d(off)}$	$V_{CC}= 600V$ $I_C= 150A$	$T_{vj}= 25^{\circ}C$		0.40	$\mu s$	
			$T_{vj}= 125^{\circ}C$		0.44		
			$T_{vj}= 150^{\circ}C$		0.45		
Fall Time, Inductive load	$t_f$	$V_{GE}= 15V$ $R_G= 10\Omega$	$T_{vj}= 25^{\circ}C$		0.14	$\mu s$	
			$T_{vj}= 125^{\circ}C$		0.23		
			$T_{vj}= 150^{\circ}C$		0.25		
Turn-On Energy	$E_{on}$		$T_{vj}= 25^{\circ}C$		14.1	mJ	
			$T_{vj}= 125^{\circ}C$		20.9		
			$T_{vj}= 150^{\circ}C$		23.5		
Turn-Off Energy	$E_{off}$		$T_{vj}= 25^{\circ}C$		8.9	mJ	
			$T_{vj}= 125^{\circ}C$		11.1		
			$T_{vj}= 150^{\circ}C$		12.0		
SC Data	$I_{sc}$	$V_{CC}= 600V$ $R_G= 20\Omega$ $V_{GE}\leq 15V$ $V_{CEmax}=V_{CE-L_{SCE}}*di/dt$	$t_p\leq 10\mu s$ $T_{vj}= 150^{\circ}C$		600	A	

### Diode, Inverter

Description	Symbols	Conditions	Values			Unit
			Min	Typ	Max	
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 150A, V <sub>GE</sub> = 0V	T <sub>vj</sub> = 25°C	2.04	2.7	V
			T <sub>vj</sub> = 125°C	1.62		
			T <sub>vj</sub> = 150°C	1.56		
Recovery Charge	Q <sub>r</sub>	I <sub>F</sub> = 150A, V <sub>R</sub> = 600V -di <sub>F</sub> /dt= 1200A/us V <sub>GE</sub> = -15V	T <sub>vj</sub> = 25°C	5.07		μC
			T <sub>vj</sub> = 125°C	15.99		
			T <sub>vj</sub> = 150°C	19.33		
Reverse Recovery Energy	E <sub>rec</sub>	I <sub>F</sub> = 150A, V <sub>R</sub> = 600V -di <sub>F</sub> /dt=1200A/us V <sub>GE</sub> = -15V	T <sub>vj</sub> = 25°C	1.88		mJ
			T <sub>vj</sub> = 125°C	5.76		
			T <sub>vj</sub> = 150°C	6.89		

### Thermal resistance

Items	Symbols	Values			Unit
		Min	Typ	Max	
Thermal Resistance, Per IGBT Junction to Case	R <sub>th(j-c)</sub>			0.3	K/W
Thermal Resistance, Per Diodes Junction to Case	R <sub>th(j-c)</sub>			0.4	

### Module

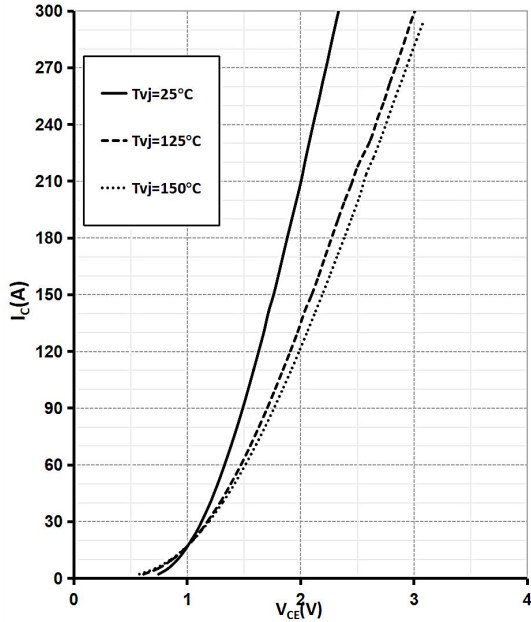
Description	Symbols	Conditions	Values	Unit
Isolation Test Voltage	V <sub>ISOL</sub>	RMS, f =50Hz, t= 1min	4.0	KV
Material of Module Base plat			Cu	
Internal Isolation			Al <sub>2</sub> O <sub>3</sub>	
Creepage Distance	d <sub>Creep</sub>	Terminal to terminal	20.1	mm
Clearance	d <sub>Clear</sub>	Terminal to terminal	9.5	mm
Comparative Tracking Index	CTI		200	

Description	Symbols	Conditions	Values			Unit
			Min	Typ	Max	
Stray Inductance Module	L <sub>sCE</sub>			29.2		nH
Module Lead Resistance , Terminals-Chip	R <sub>CC'+EE'</sub>	T <sub>C</sub> = 25°C, Per switch		0.66		mΩ
Mounting Torque for Module Mounting	M	Screw M5	3.0		5.0	Nm
Weight	G			156		g

**Output characteristic (typical), IGBT, Inverter**

$I_C = f(V_{CE})$

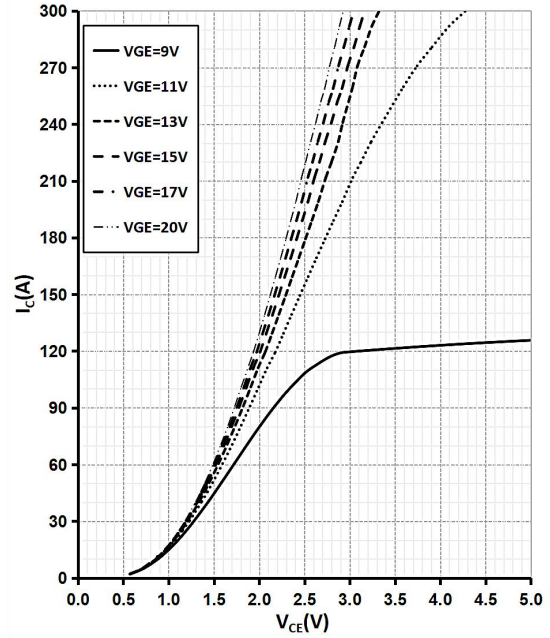
$V_{GE} = 15V$



**Output characteristic (typical), IGBT, Inverter**

$I_C = f(V_{CE})$

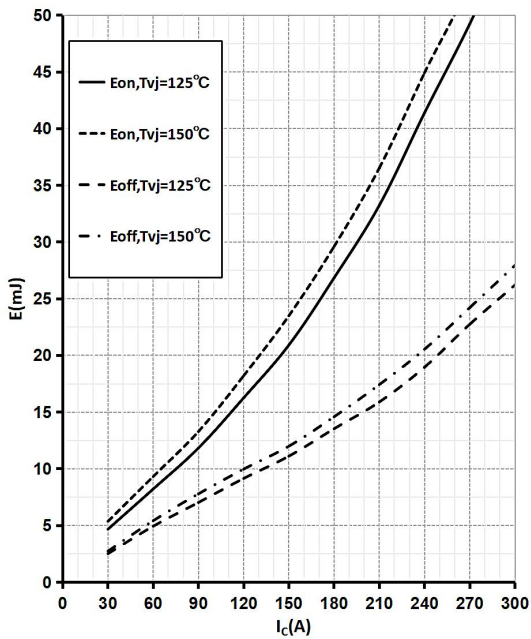
$T_{vj} = 150^{\circ}C$



**Switching losses (typical), IGBT, Inverter**

$E = f(I_C)$

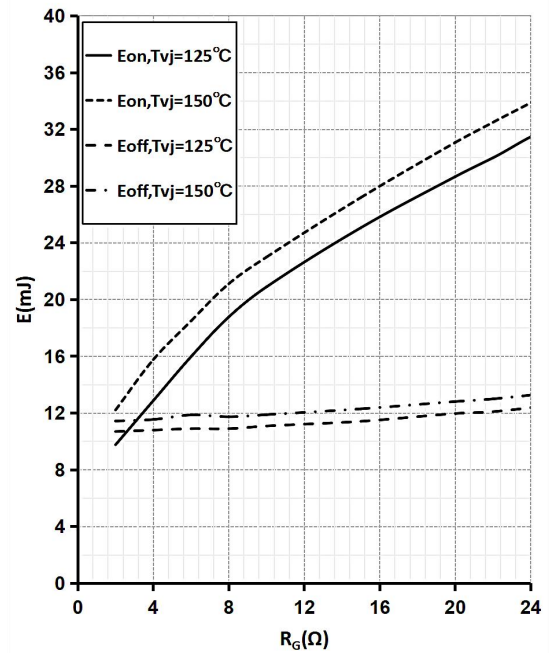
$R_{Goff} = 10\Omega, R_{Gon} = 10\Omega, V_{GE} = \pm 15V, V_{CC} = 600V$



**Switching losses (typical), IGBT, Inverter**

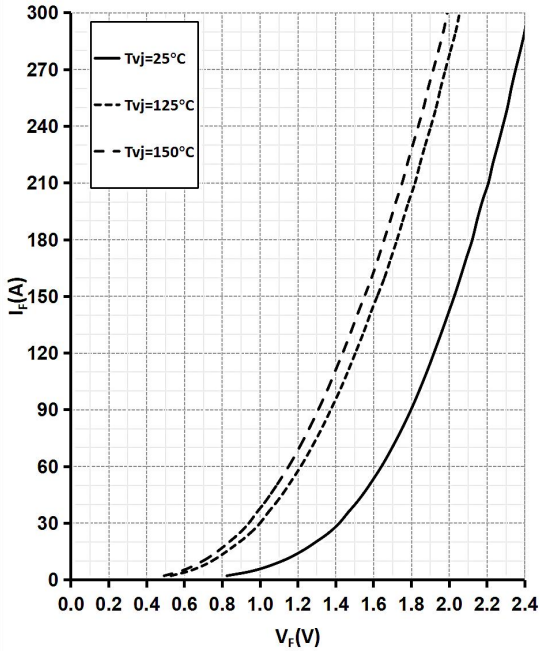
$E = f(R_G)$

$V_{GE} = 15V, I_C = 150A, V_{CC} = 600V$



**Forward characteristic (typical), Diode, Inverter**

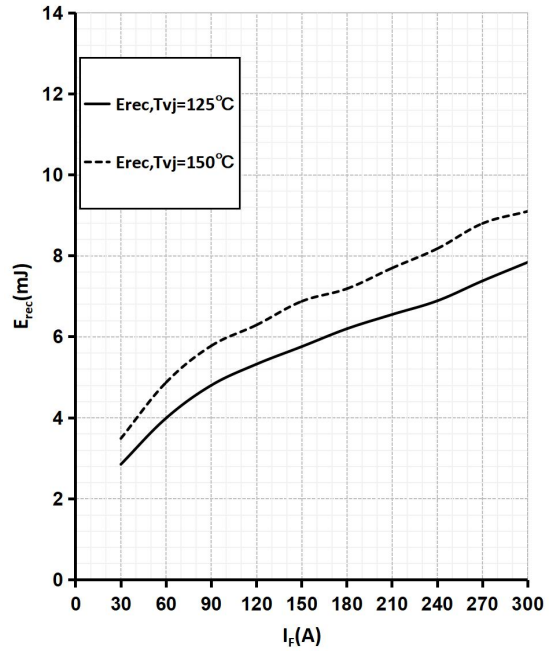
$$I_F = f(V_F)$$



**Switching losses (typical), Diode, Inverter**

$$E_{rec} = f(I_F)$$

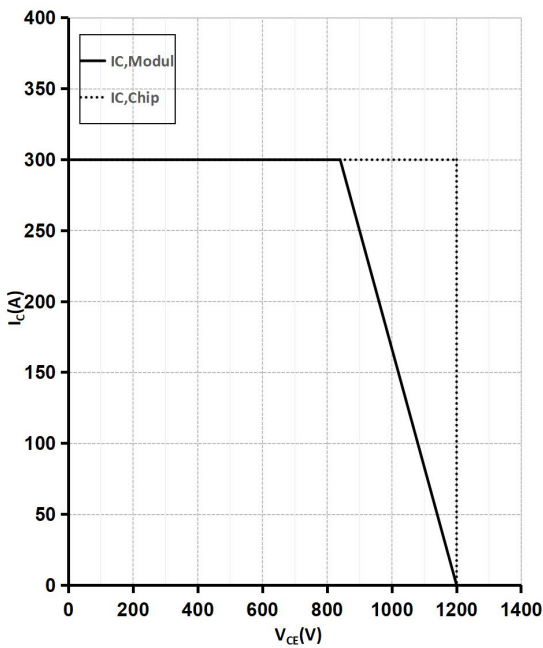
$$R_{Gon} = 10\Omega, V_{CC} = 600V$$



**Reverse bias safe operating area (RBSOA), IGBT, Inverter**

$$I_C = f(V_{CE})$$

$$R_{Goff} = 10\Omega, V_{GE} = \pm 15V, T_{vj} = 150^\circ C$$





## Revision History

Revision	Date	Subjects (major changes since last revision)
0.1	2023-04-10	Preliminary version
1.0	2023-11-23	MP version

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